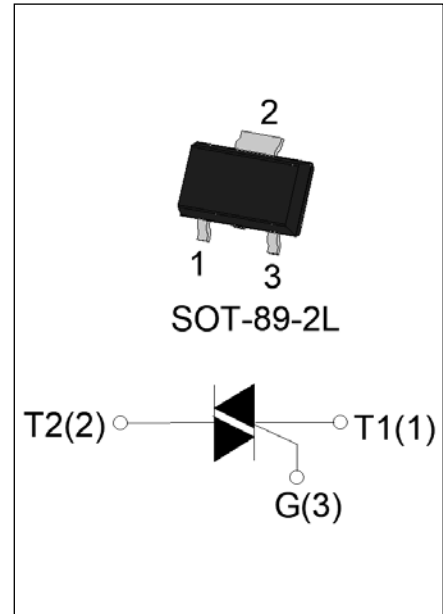


JST131N2-600T 1A TRIAC

Rev.A.1.1

DESCRIPTION:

The JST131N2-600T triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Package SOT-89-2L is RoHS compliant.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\ I/II/III/IV}$	5/5/5/5	mA

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	°C
Operating junction temperature range		T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)		V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)		V_{RRM}	600	V
RMS on-state current ($T_c \leq 58^\circ\text{C}$)		$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)		I_{TSM}	16.5	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)			18	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)		I^2t	1.36	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100\text{Hz}$, $T_j=125^\circ\text{C}$)	I - II	di/dt	30	$\text{A}/\mu\text{s}$
	III-IV		20	
Peak gate current ($t_p=20\mu\text{s}$, $T_j=125^\circ\text{C}$)		I_{GM}	2	A
Average gate power dissipation ($T_j=125^\circ\text{C}$)		$P_{G(AV)}$	0.5	W
Peak gate power		P_{GM}	5	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.8)		V_{PP}	3.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	ALL	MAX.	5	mA
V_{GT}		ALL	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{k}\Omega$	ALL	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III-IV	MAX.	5	mA
		II		10	
I_H	$I_T=50\text{mA}$		MAX.	5	mA
dV/dt	$V_D=400\text{V}$ Gate Open $T_j=110^\circ\text{C}$		MIN.	30	V/ μs
(dV/dt) _c	(dI/dt) _c =0.44A/ms, $T_j=110^\circ\text{C}$		MIN.	1	V/ μs
t_{on}	$I_G=10\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	2	μs
t_{off}				20	

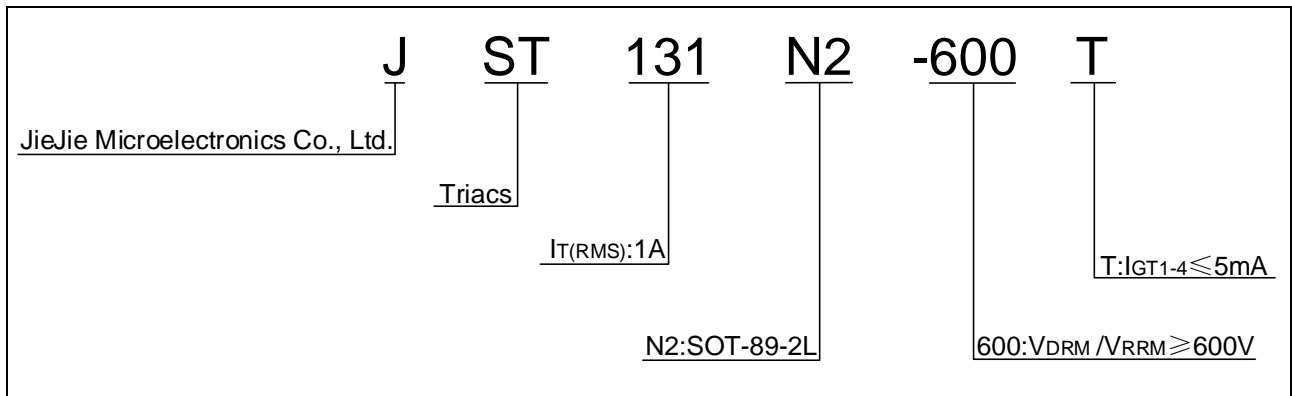
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.4\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.45	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.96	V
R_D	Dynamic resistance	$T_j=125^\circ\text{C}$	225	m Ω
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	0.2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	50	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC, in free air, $S=5\text{cm}^2$)	100	$^\circ\text{C}/\text{W}$

ORDERING INFORMATION



MARKING

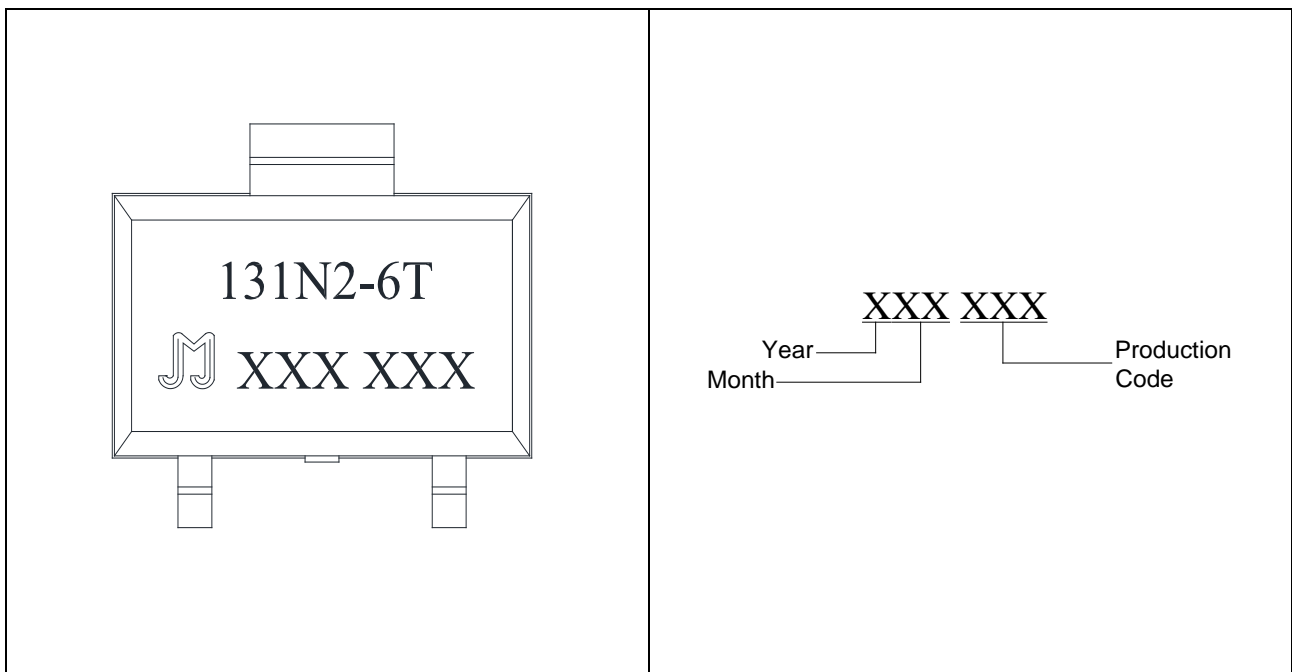


FIG.1: Maximum power dissipation versus RMS on-state current

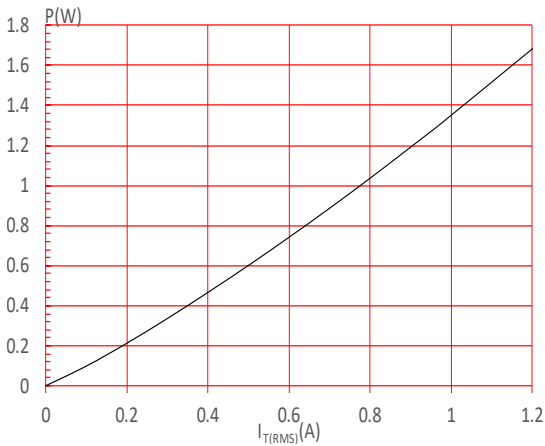


FIG.3: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35μm) (full cycle)

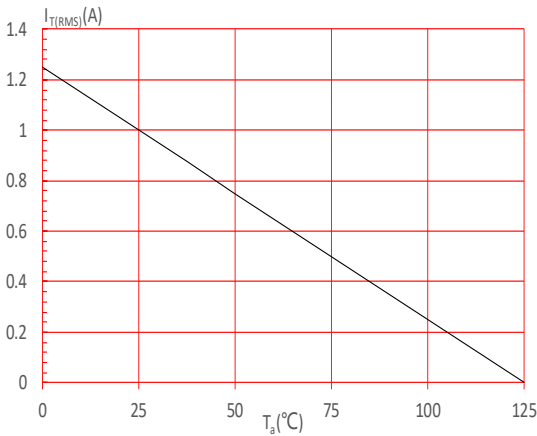


FIG.5: On-state characteristics

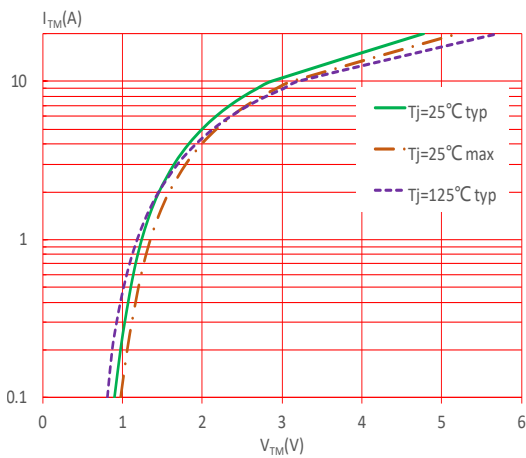


FIG.2: RMS on-state current versus case temperature

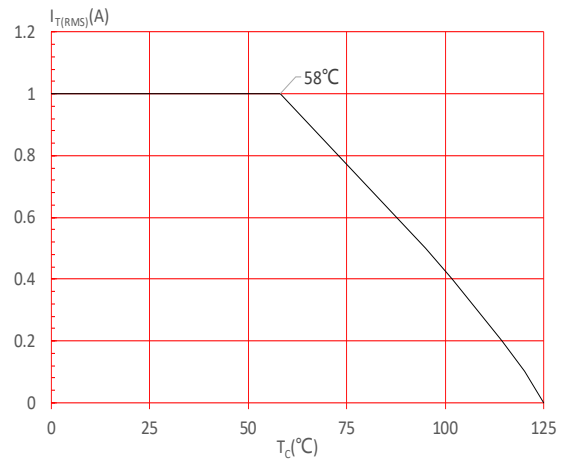


FIG.4: Surge peak on-state current versus number of cycles

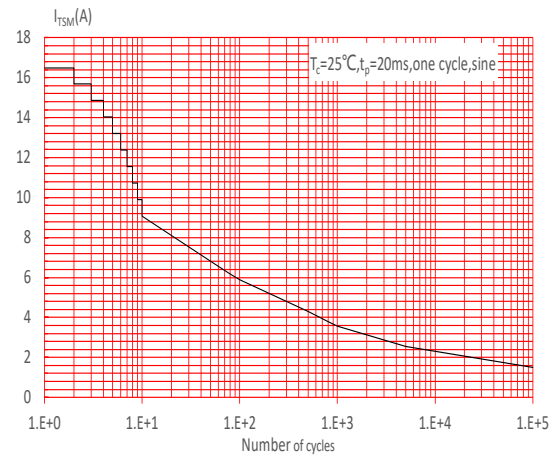


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II: $di/dt < 30\text{A}/\mu\text{s}$; III-IV: $di/dt < 20\text{A}/\mu\text{s}$)

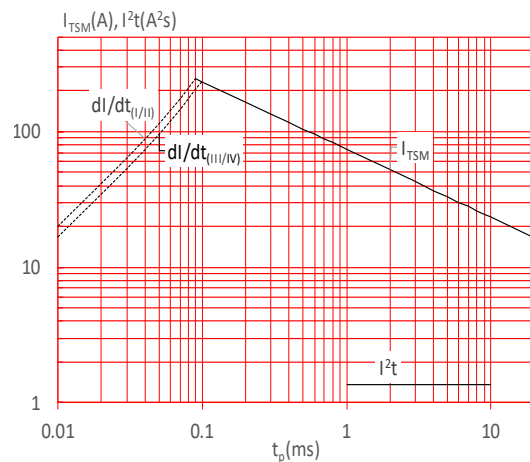


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

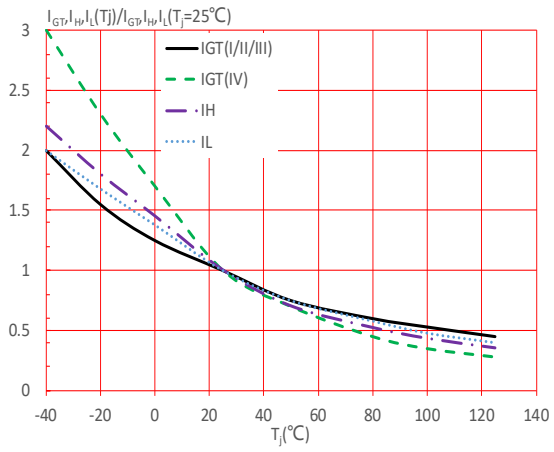
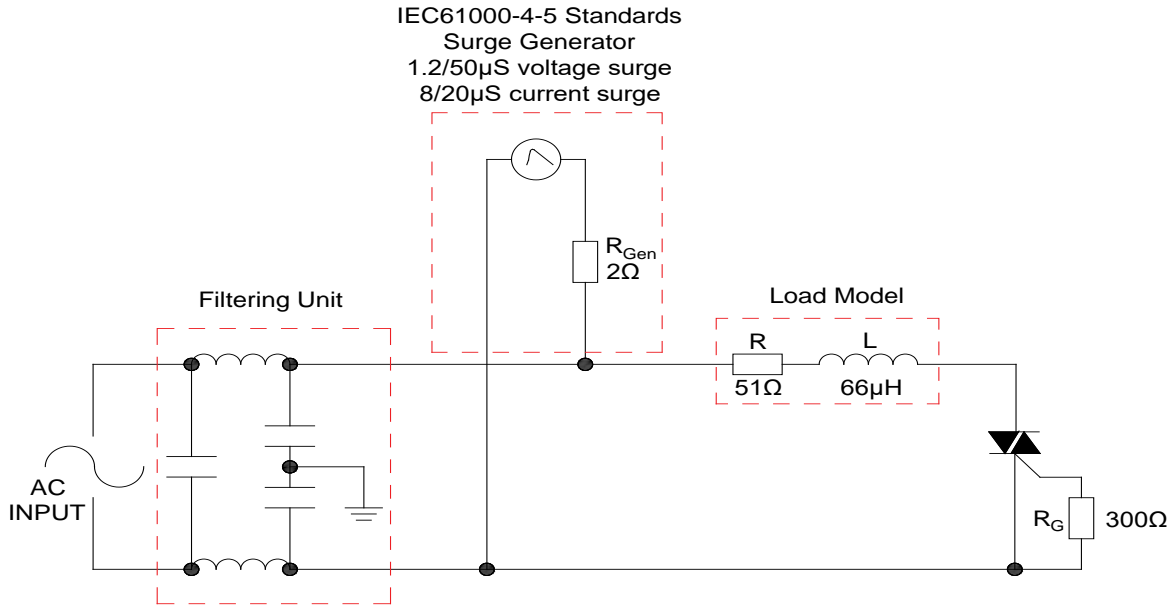
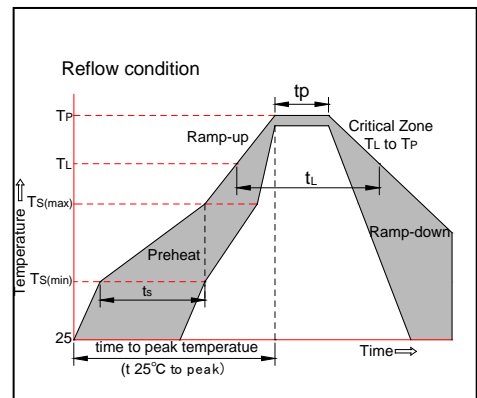


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260°C



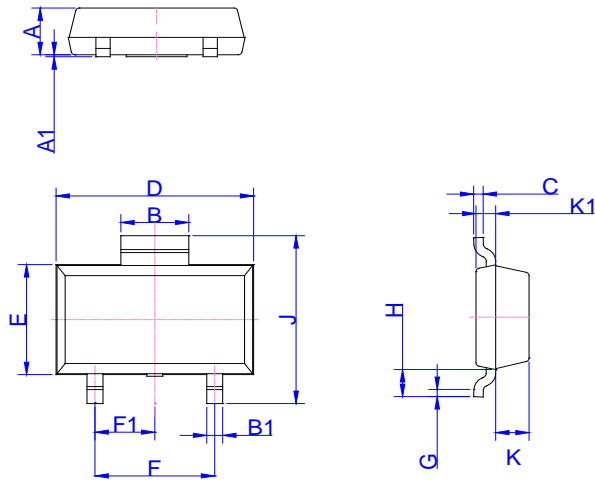
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I -II-III-IV			
JST131N2-600T	600	5	SOT-89-2L	4,000	Tape & Reel

Document Revision History

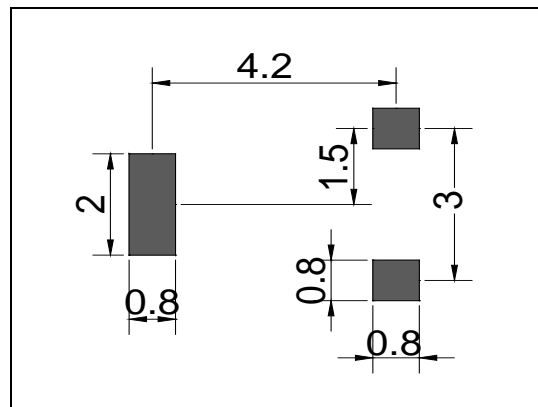
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated
Oct.16, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.3	1.4	1.5	0.051	0.055	0.059
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	1.6	1.7	1.8	0.063	0.067	0.071
B1	0.3	0.4	0.5	0.012	0.016	0.020
C	0.22	0.254	0.32	0.009	0.010	0.013
D	4.75	4.95	5.15	0.187	0.195	0.203
E	2.90		3.30	0.114		0.130
F	2.80		3.20	0.110		0.126
F1	1.40		1.60	0.055		0.063
G	0.20	0.30	0.40	0.008	0.012	0.016
H	0.58	0.78	0.98	0.023	0.031	0.039
J	4.30	4.50	4.70	0.169	0.177	0.185
K	0.80		1.00	0.031		0.039
K1	0.50		0.60	0.020		0.024

FOOTPRINT-SOT-89-2L (dimensions in mm)



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